

GL Silicon N-Channel Power MOSFET

General Description

The GL1S20N06L-D8 uses advanced trench technology and design to provide excellent RDS(ON) with low gate charge. It can be used in a wide variety of applications. The package form is SOP-8, which accords with the RoHS standard and two dies in this form.

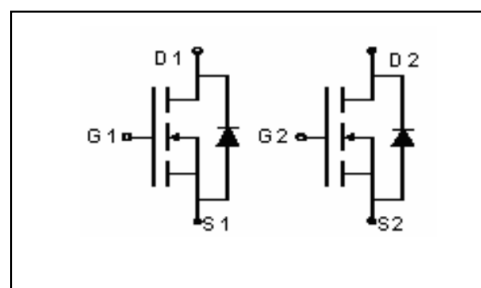
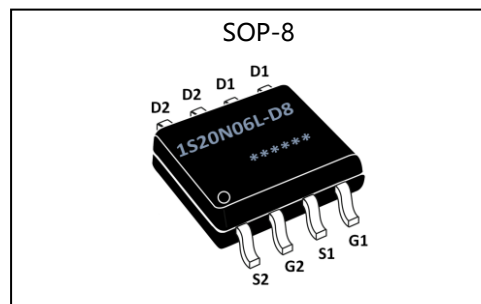
Features

- Fast Switching
- Low Gate Charge and Rdson
- Low Reverse transfer capacitances
- 100% Single Pulse avalanche energy Test

Applications

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

V_{DSS}	60	V
I_D	20	A
P_D	2.1	W
$R_{DS(ON)}$	30	mΩ



Absolute (Tc= 25°C unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DSS}	Drain-to-Source Voltage	60	V
I_D	Continuous Drain Current	20	A
	Continuous Drain Current $T_C = 100\text{ }^{\circ}\text{C}$	6	A
I_{DM}	Pulsed Drain Current	32	A
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}^{a2}	Single Pulse Avalanche Energy	72	mJ
E_{AR}^{a1}	Avalanche Energy ,Repetitive	18	mJ
I_{AR}^{a1}	Avalanche Current	11	A
dv/dt^{a3}	Peak Diode Recovery dv/dt	5.0	V/ns
P_D	Power Dissipation	2.1	W
T_J, T_{stg}	Operating Junction and Storage Temperature Range	175, -55 to 175	$^{\circ}\text{C}$
T_L	Maximum Temperature for Soldering	300	$^{\circ}\text{C}$

**GL Silicon N-Channel Power MOSFET****Electrical Characteristics** (Tc= 25°C unless otherwise specified)

OFF Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
V_{DSS}	Drain to Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	60	--	--	V
$\Delta BV_{DSS}/\Delta T_J$	Bvdss Temperature Coefficient	$I_D=250\mu A, \text{Reference } 25^\circ C$	--	0.1	--	V/°C
I_{DSS}	Drain to Source Leakage Current	$V_{DS}=60V, V_{GS}=0V, T_a=25^\circ C$	--	--	1	μA
		$V_{DS}=48V, V_{GS}=0V, T_a=125^\circ C$	--	--	250	
$I_{GSS(F)}$	Gate to Source Forward Leakage	$V_{GS}=+20V$	--	--	1	μA
$I_{GSS(R)}$	Gate to Source Reverse Leakage	$V_{GS}=-20V$	--	--	-1	μA

ON Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$R_{DS(ON)}$	Drain-to-Source On-Resistance	$V_{GS}=10V, I_D=8A$	--	30	40	m Ω
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.7	2.5	V
Pulse width $t_p \leq 380\mu s, \delta \leq 2\%$						

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
g_{fs}	Forward Transconductance	$V_{DS}=5V, I_D=8A$	18	--	--	S
C_{iss}	Input Capacitance	$V_{GS}=0V, V_{DS}=30V$ $f=1.0MHz$	--	500	--	pF
C_{oss}	Output Capacitance		--	60	--	
C_{rss}	Reverse Transfer Capacitance		--	25	--	

Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
$t_{d(ON)}$	Turn-on Delay Time	$I_D=2A, V_{DD}=30V$ $V_{GS}=10V, R_G=3.0\Omega$	--	5	--	ns
t_r	Rise Time		--	2.6	--	
$t_{d(OFF)}$	Turn-Off Delay Time		--	2.3	--	
t_f	Fall Time		--	5.5	--	
Q_g	Total Gate Charge	$I_D=4.5A, V_{DD}=30V$ $V_{GS}=10V$	--	47	--	nC
Q_{gs}	Gate to Source Charge		--	6	--	
Q_{gd}	Gate to Drain ("Miller") Charge		--	14	--	

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Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
I_S	Continuous Source Current (Body Diode)		--	--	8	A
I_{SM}	Maximum Pulsed Current (Body Diode)		--	--	32	A
V_{SD}	Diode Forward Voltage	$I_S=8A, V_{GS}=0V$	--	--	1.5	V
t_{rr}	Reverse Recovery Time	$I_S=8A, T_j = 25^\circ C$	--	28	--	ns
Q_{rr}	Reverse Recovery Charge	$di_F/dt=100A/us, V_{GS}=0V$	--	40	--	nC
Pulse width $tp \leq 380\mu s, \delta \leq 2\%$						

Symbol	Parameter	Typ.	Units
$R_{\theta JA}$	Junction-to-Ambient	60	$^\circ C/W$

a¹: Repetitive rating; pulse width limited by maximum junction temperature

a²: EAS condition : $T_j=25, V_{DD}=30V, V_G=10V, L=0.5mH, R_g=25\Omega$

a³: $I_{SD}=10A, di/dt \leq 100A/us, V_{DD} \leq BV_{DS}, \text{Start } T_j=25^\circ C$

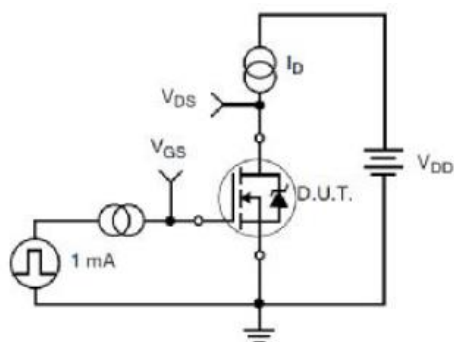
Test Circuit and Waveform


Figure 17. Gate Charge Test Circuit

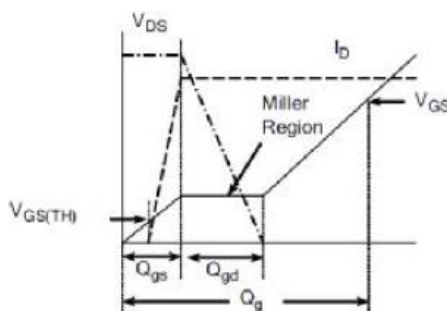


Figure 18. Gate Charge Waveform

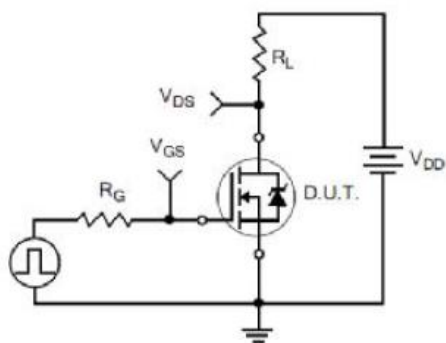


Figure 19. Resistive Switching Test Circuit

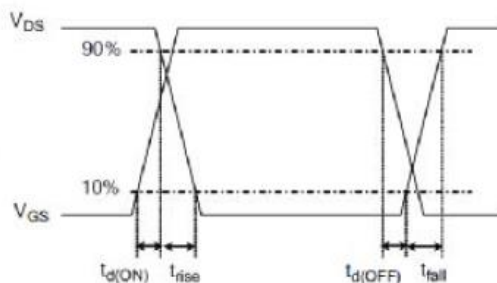
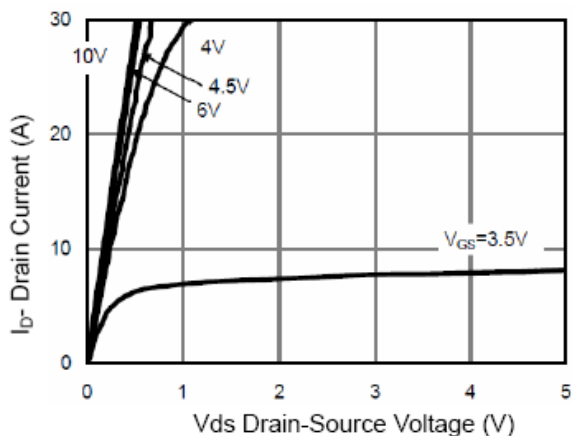
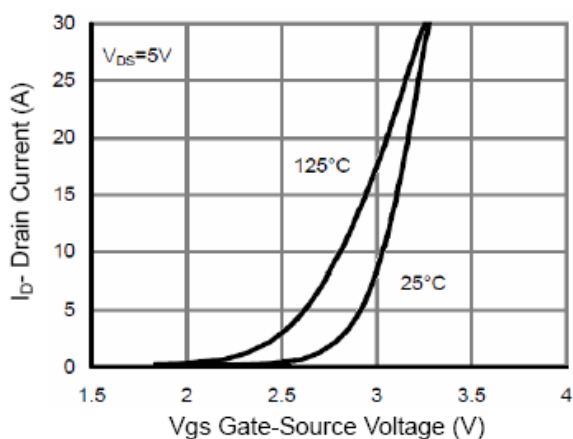
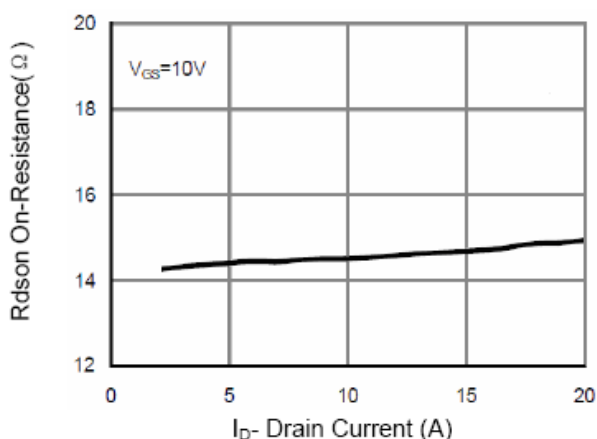
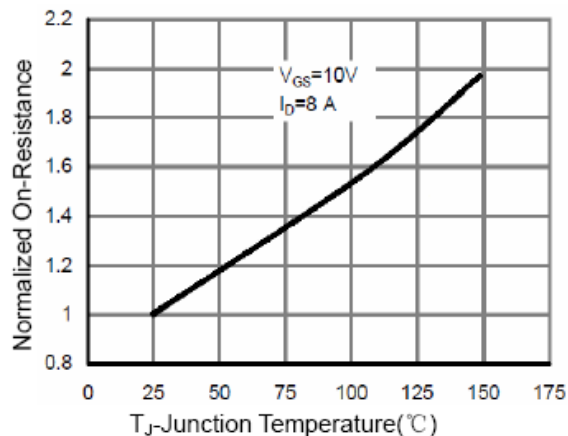
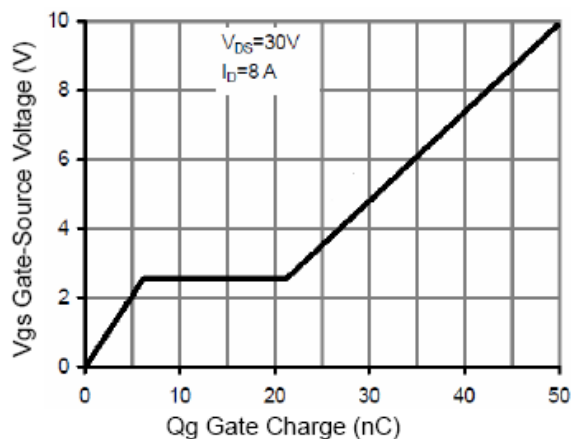
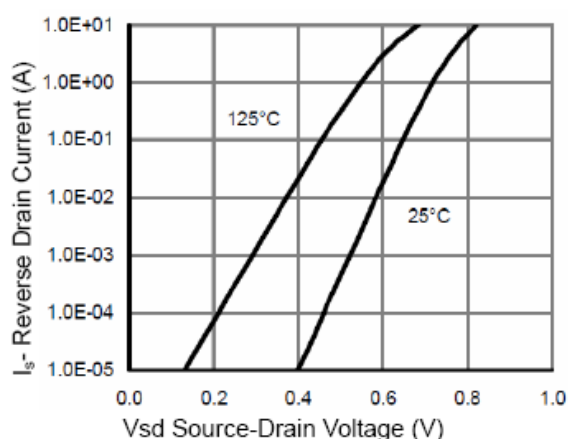
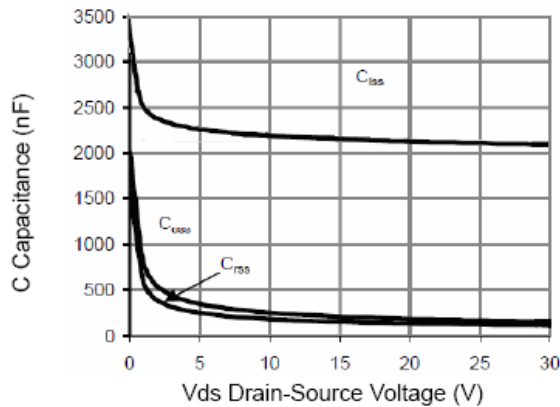
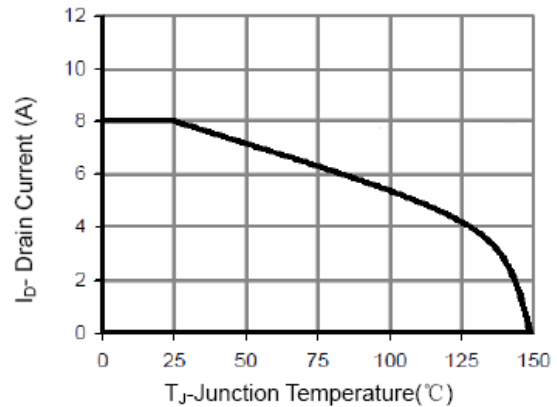
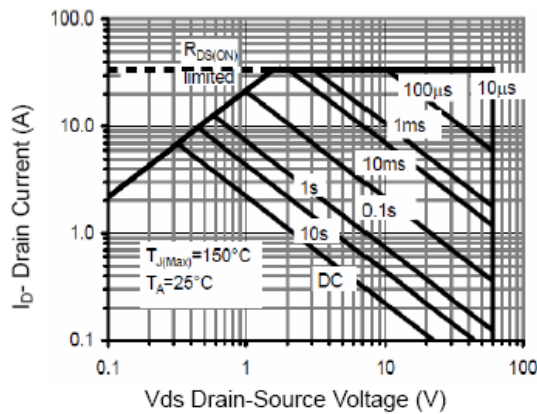
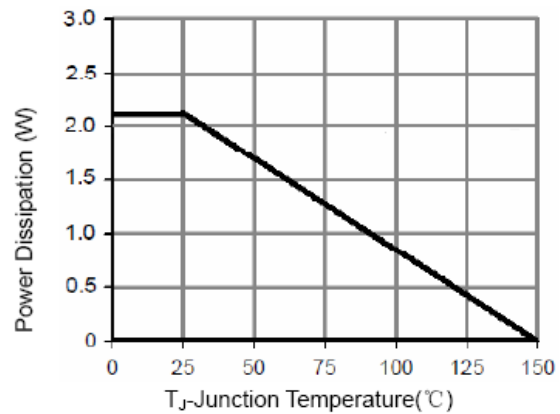
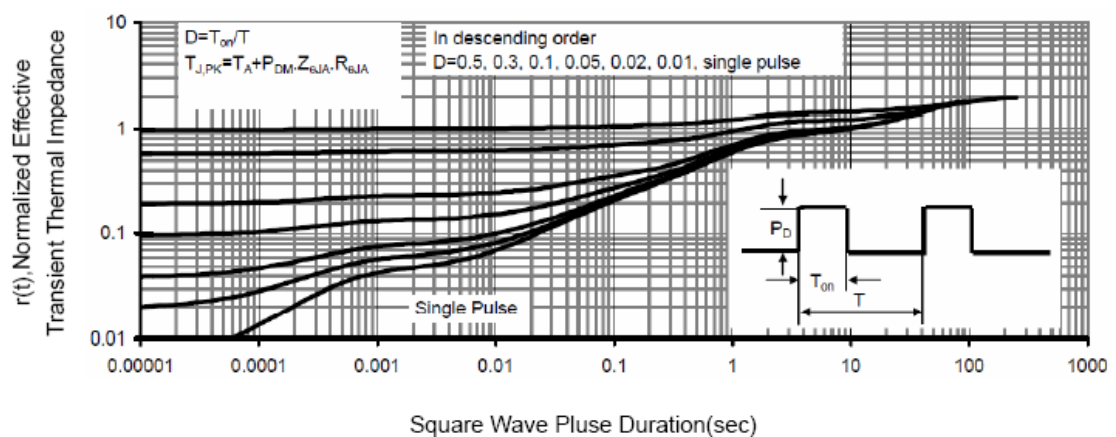


Figure 20. Resistive Switching Waveforms

GL Silicon N-Channel Power MOSFET
Characteristics Curve

Figure 1 Output Characteristics

Figure 2 Transfer Characteristics

Figure 3 Rdson- Drain Current

Figure 4 Rdson-Junction Temperature

Figure 5 Gate Charge

Figure 6 Source- Drain Diode Forward

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Figure 7 Capacitance vs Vds

Figure 9 Current De-rating

Figure 8 Safe Operation Area

Figure 10 Power De-rating

Figure 11 Normalized Maximum Transient Thermal Impedance

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